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December 2013

### FDP75N08A

### N-Channel UniFET™ MOSFET

75 V, 75 A, 11 mΩ

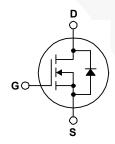
#### **Features**

- 75 A, 75 V,  $R_{DS(on)}$  = 11 m $\Omega$  @  $V_{GS}$  = 10 V Low Gate Charge (Typ. 145 nC)
- Low Crss (Typ. 86 pF)
- · Fast Switching
- · Improved dv/dt Capability

### **Description**

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FDP75N08A	Unit	
V <sub>DSS</sub>	Drain-Source Voltage	75	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)	75	Α	
	- Continuous (T <sub>C</sub> = 100°C)	47	Α	
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	300	Α	
V <sub>GSS</sub>	Gate-Source Voltage	± 20	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	1738	mJ	
I <sub>AR</sub>	Avalanche Current (Note 1)	75	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	13.7	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)	137	W	
	- Derate Above 25°C		W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8 from Case for 5 Seconds	300	°C	

### **Thermal Characteristics**

Symbol	Parameter	FDP75N08A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.91	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

## **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP75N08A	FDP75N08A	TO-220	Tube	N/A	50 units

### Electrical Characteristics TC = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	75			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$ , Referenced to 25°C		0.6		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 0 V			1	μА
		V <sub>DS</sub> = 60 V, T <sub>C</sub> = 125°C			10	μА
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Charact	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 37.5 A		9.4	11	mΩ
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 37.5 A		15		S
Dynamic Cl	haracteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		3437	4468	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		738	959	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			86	129	pF
Switching C	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 37.5 \text{ V}, I_D = 75\text{A},$		43	95	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		212	434	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			273	556	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		147	303	ns
Qg	Total Gate Charge	$V_{DS} = 60 \text{ V}, I_{D} = 75\text{A},$		80	104	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V	/	20		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		24		nC
Drain-Source	ce Diode Characteristics and Maximum Ratings	5			· /	
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				75	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				300	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 75 \text{ A}$			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_S = 75 \text{ A},$		62		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$		145		nC

 $<sup>\</sup>begin{tabular}{ll} \textbf{Notes:} \\ 1: & \textbf{Repetitive rating: pulse-width limited by maximum junction temperature.} \\ 2: & \textbf{L} = 206 \ \mu \textbf{H}, \ \textbf{I}_{AS} = 75 \ \textbf{A}, \ \textbf{V}_{DD} = 50 \ \textbf{V}, \ \textbf{R}_{G} = 25 \ \Omega, \ \textbf{starting} \ \textbf{T}_{J} = 25 ^{\circ} \textbf{C}. \\ 3: & \ \textbf{I}_{SD} \le 75 \textbf{A}, \ \textbf{d}i/\textbf{d}t \le 200 \ \textbf{A}/\textbf{us}, \ \textbf{V}_{DD} \le \textbf{BV}_{DS}, \ \textbf{starting} \ \textbf{T}_{J} = 25 ^{\circ} \textbf{C}. \\ 4: & \ \textbf{Essentially independent of operating temperature typical characteristics.} \\ \end{tabular}$ 

### **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

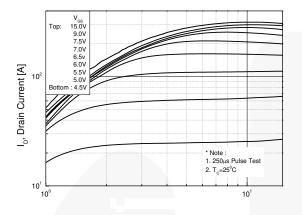


Figure 2. Transfer Characteristics

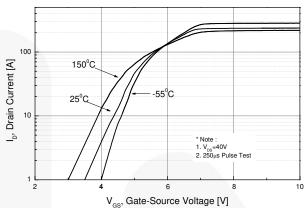
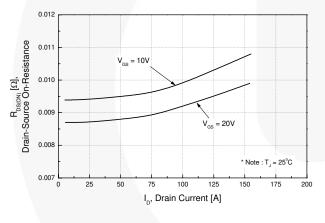
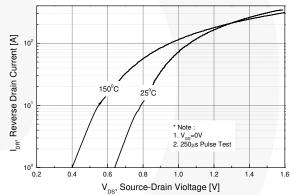


Figure 3. On-Resistance Variation vs.

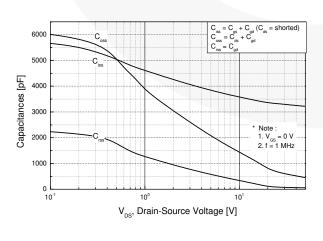
Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

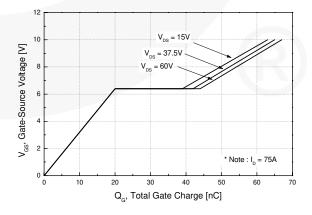




**Figure 5. Capacitance Characteristics** 



**Figure 6. Gate Charge Characteristics** 



### Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

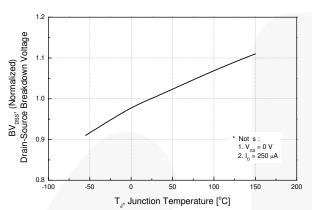


Figure 8. On-Resistance Variation vs. Temperature

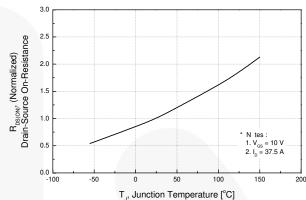


Figure 9. Maximum Safe Operating Area

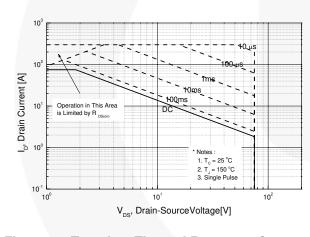


Figure 10. Maximum Drain Current vs. Case Temperature

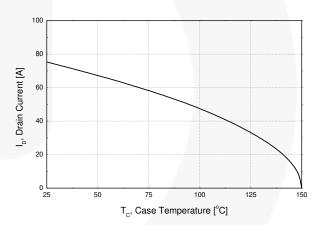


Figure 11. Transient Thermal Response Curve

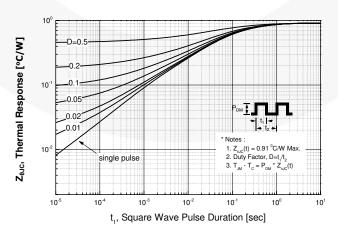


Figure 12. Gate Charge Test Circuit & Waveform

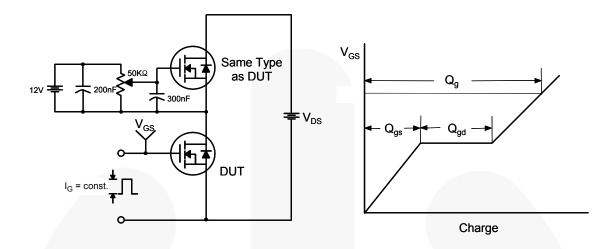


Figure 13. Resistive Switching Test Circuit & Waveforms

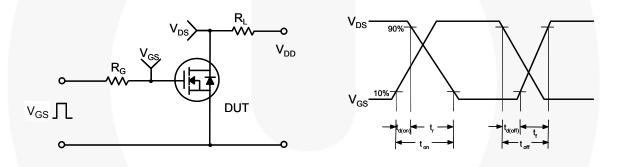
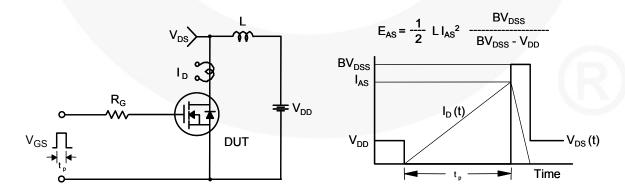


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



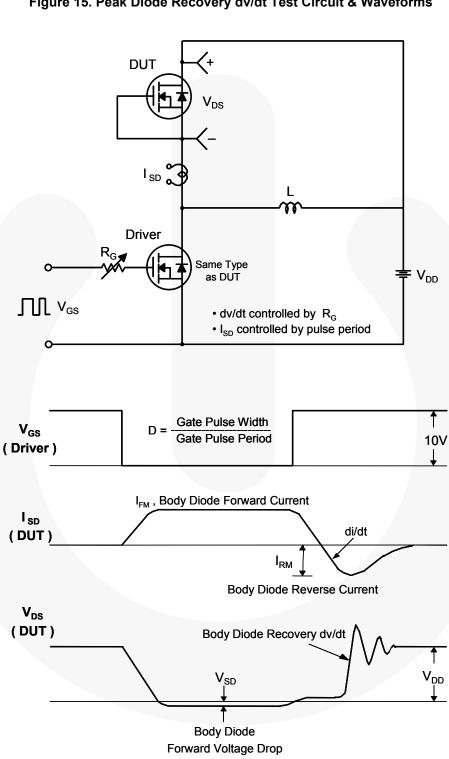


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

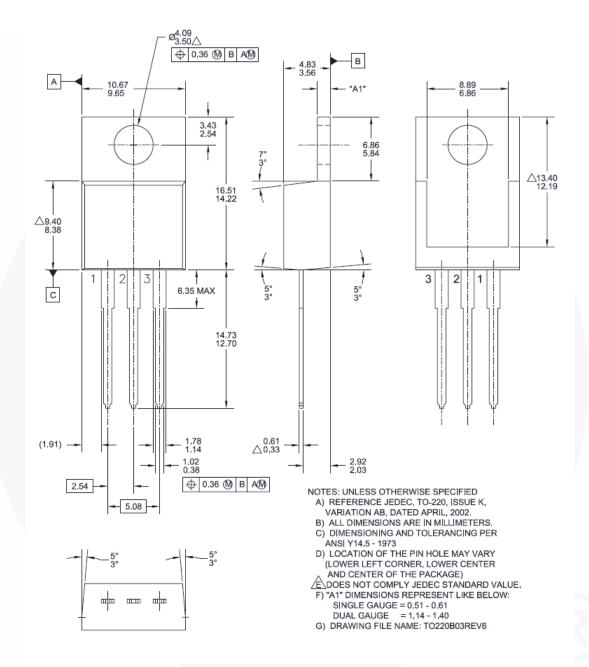


Figure 16. TO-220, Molded, 3Lead, Jedec Variation AB

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